

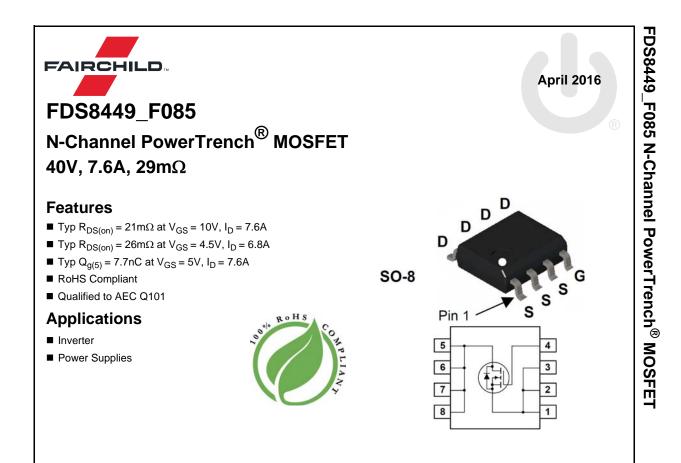
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MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain to Source Voltage		40	V	
V _{GS}	Gate to Source Voltage		±20	V	
I _D	Drain Current Continuous (V _{GS} = 10V)		7.6	^	
	Pulsed		50	Α	
E _{AS}	Single Pulse Avalanche Energy (N	lote 1)	27	mJ	
P _D	Power Dissipation		5	W	
	Derate above 25°C		0.04	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature		-55 to +150	°C	
$R_{\theta JC}$	Thermal Resistance Junction to Case		25	°C/W	
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, 1in ² copper pad area		50	°C/W	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS8449	FDS8449_F085	SO-8	13"	12mm	2500 units

Notes:

1: Starting $T_J = 25^{\circ}$ C, L = 1mH, I_{AS} = 7.3A, V_{DD} = 40V. 2: A suffix as "...F085P" has been temporarily introduced in order to manage a double source strategy as Fairchild has officially announced in Aug 2014.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics					
B _{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40	-	-	V
	Zero Gate Voltage Drain Current	V _{DS} = 32V,	-	-	1	
IDSS	Zero Gale voltage Drain Current	$V_{GS} = 0V$ $T_A = 150^{\circ}C$	-	-	250	μA
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20V$	-	-	±100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$ $I_D = 7.6A, V_{GS} = 10V$	1	1.9 21	3 29	V
On Cha	racteristics					
		$I_D = 7.6$ A, $V_{GS} = 10$ V $I_D = 6.8$ A, $V_{GS} = 4.5$ V	-	21	36	_
r _{DS(on)}	Drain to Source On Resistance	$I_D = 7.6A, V_{GS} = 10V$ $T_J = 125^{\circ}C$	-	29	43	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 10V, I _D = 7.6A	-	21	-	S
-	c Characteristics			Γ		
C _{iss}	Input Capacitance	V _{DS} = 20V, V _{GS} = 0V,	-	760	-	pF
C _{oss}	Output Capacitance	f = 1MHz	-	100	-	pF
C _{rss}	Reverse Transfer Capacitance		-	60	-	pF
R _G	Gate Resistance	f = 1MHz	-	1.2	-	Ω
Q _{g(TOT)}	Total Gate Charge at 10V	$V_{GS} = 0 \text{ to } 5V$ $V_{DD} = 20V$	-	7.7	11	nC
Q _{gs}	Gate to Source Gate Charge	$V_{DD} = 20V$ $I_{D} = 7.6A$	-	2.4	-	nC
Q _{ad}	Gate to Drain "Miller" Charge	.0		2.8	-	nC

Switching Characteristics

Gate to Drain "Miller" Charge

 Q_{gd}

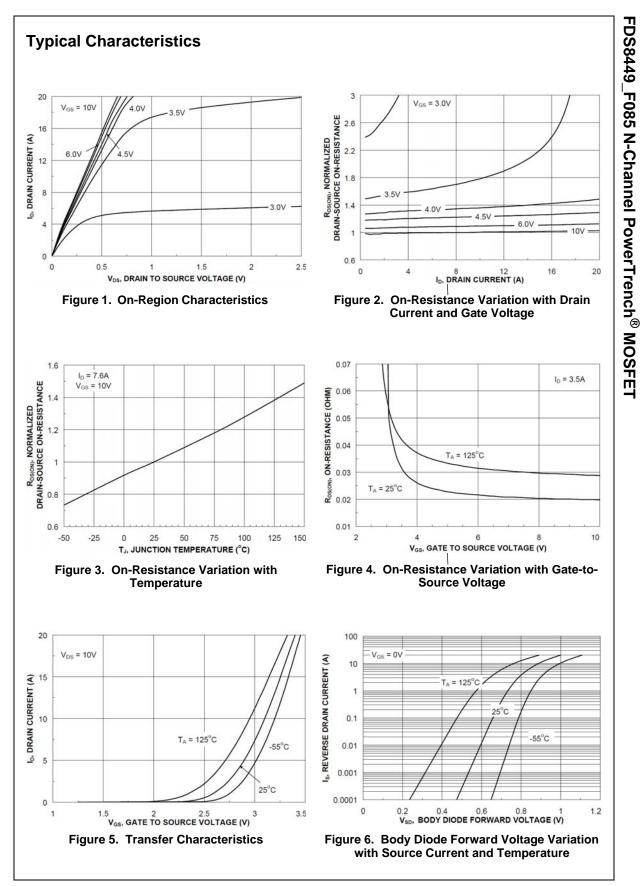
t _{on}	Turn-On Time		-	-	21	ns
t _{d(on)}	Turn-On Delay Time		-	9	-	ns
t _r	Rise Time	$V_{DD} = 20V, I_D = 1A$ $V_{GS} = 10V, R_{GEN} = 6\Omega$	-	5	-	ns
t _{d(off)}	Turn-Off Delay Time	$v_{GS} = 10v, R_{GEN} = 0sz$	-	23	-	ns
t _f	Fall Time		-	3	-	ns
t _{off}	Turn-Off Time		-	-	39	ns

2.8

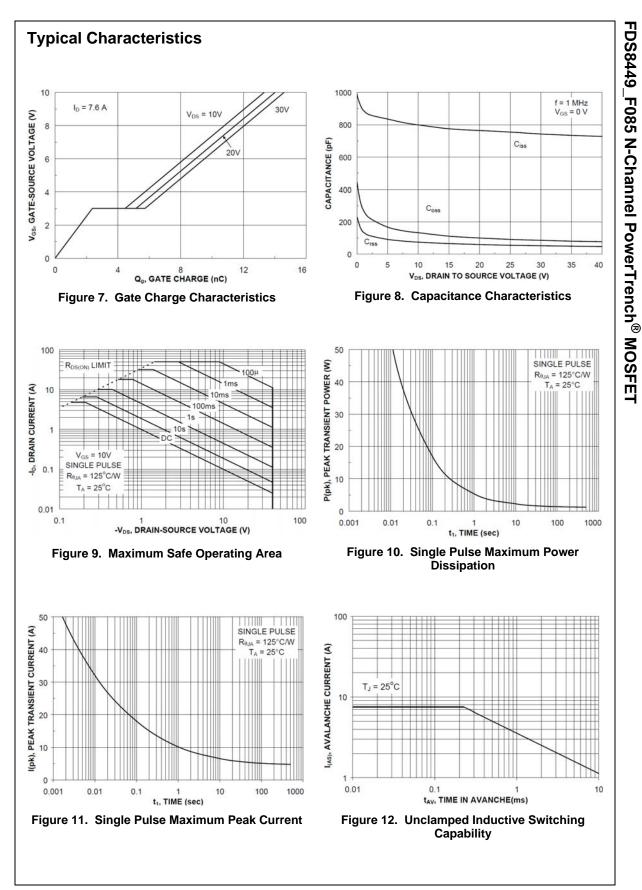
nC

Drain-Source Diode Characteristics

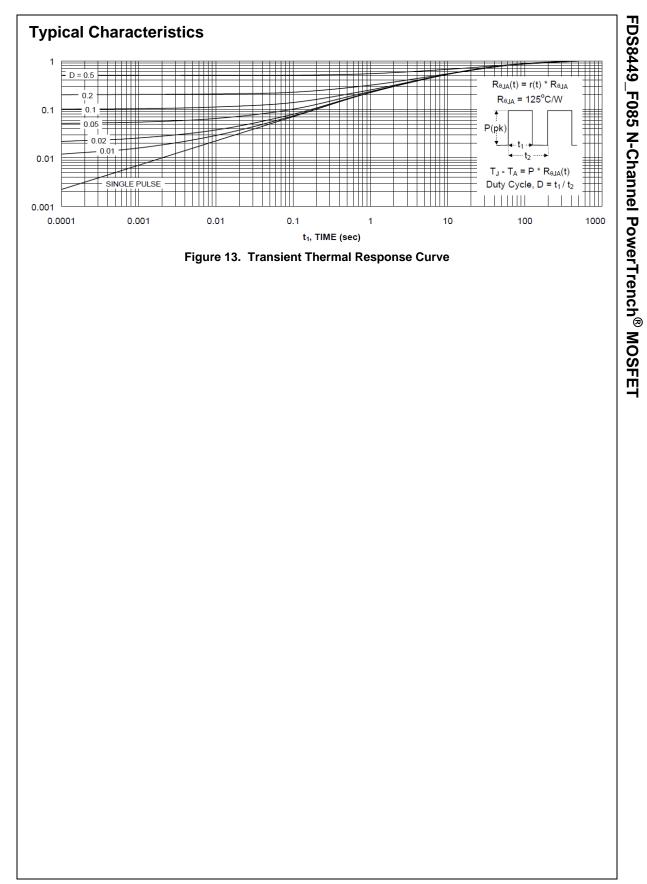
V_{SD}	Source to Drain Diode Voltage	I _{SD} = 2.1A	-	0.76	1.2	V
t _{rr}	Reverse Recovery Time	––– I _{SD} = 7.6A, dI _{SD} /dt = 100A/μs	-	17	-	ns
Q _{rr}	Reverse Recovery Charge		-	7	-	nC



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